

ABSTRACT OF THE DISCLOSURE

The invention includes methods of depositing elemental silicon-comprising materials over a semiconductor substrate, and methods of cleaning an internal wall of a chamber. In one implementation, a semiconductor substrate is positioned within a chamber for deposition. The chamber comprises an infrared radiation transparent wall. An elemental silicon-comprising material is deposited on the semiconductor substrate. During such depositing, a deposit is formed on the infrared radiation transparent wall within the chamber. After such depositing, a plasma is generated within the chamber with a cleaning gas from at least one plasma generating electrode received external of the chamber proximate the infrared radiation transparent wall effective to remove at least some of the deposit from the infrared radiation transparent wall within the chamber. Other aspects and implementations are contemplated.